AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A plasma CVD apparatus comprising an anode electrode and a cathode electrode, which is for forming a thin film on a substrate by performing plasma discharge between the anode electrode and the cathode electrode, comprising:

a substrate holder disposed between the anode electrode and the cathode electrode; and

one conductive member disposed between the substrate holder and one electrode of either the anode electrode or the cathode electrode, wherein

the substrate holder supports the substrate,

the one conductive member is provided between the one electrode and the substrate holder so as to substantially cover an entire space between the one electrode and the substrate holder, and

the one conductive member is electrically connected to the one electrode and the substrate holder.

2. (Original) A plasma CVD apparatus according to claim 1, wherein shapes of the anode electrode and the cathode electrode are plate-like shapes.

3. (Original) A plasma CVD apparatus according to claim 1, wherein plasma discharge is performed between the anode electrode and the cathode electrode by applying a voltage between the anode electrode and the cathode electrode with a raw material gas supplied between the anode electrode and the cathode electrode.

4. (Original) A plasma CVD apparatus according to claim 1, wherein:

the one conductive member includes a supporting plate provided substantially parallel to the one electrode and a plurality of conductive plates provided on an upper surface and a lower surface of the supporting plate;

the upper surface of the supporting plate is a surface of the supporting plate opposing the substrate holder;

the lower surface of the supporting plate is a surface of the supporting plate opposing the one electrode;

the plurality of the conductive plates provided on the upper surface of the supporting plate are in contact with the substrate holder;

the plurality of the conductive plates provided on the lower surface of the supporting plate are in contact with the one electrode;

the shapes of the plurality of the conductive plates provided on the upper surface and the lower surface of the supporting plate are leaf-spring shapes;

the plurality of conductive plates are provided on the upper surface and the lower surface of the supporting plate by attaching one edge of each of the plurality of conductive plates to the supporting plate; and

the other edge of each of the plurality of the conductive plates is spaced from the supporting plate.

5. (Original) A plasma CVD apparatus according to claim 1, wherein:

the one conductive member includes a supporting plate provided substantially parallel to the one electrode and a plurality of conductive plates provided on an upper surface and a lower surface of the supporting plate;

the upper surface of the supporting plate is a surface of the supporting plate opposing the substrate holder;

the lower surface of the supporting plate is a surface of the supporting plate opposing the one electrode;

the plurality of the conductive plates provided on the upper surface of the supporting plate are in contact with the substrate holder;

the plurality of the conductive plates provided on the lower surface of the supporting plate are in contact with the one electrode;

the plurality of the conductive plates provided on the upper surface and the lower surface of the supporting plate are curved into arc shapes; and

the plurality of conductive plates are provided on the upper surface and the lower surface of the supporting plate by attaching one edge and the other edge of each of the plurality of conductive plates provided on the upper surface and the lower surface of the supporting plate to the supporting plate.

6. (Previously presented) A plasma CVD apparatus according to claim 1, wherein:

the one conductive member includes a supporting plate provided substantially parallel to the one electrode and a plurality of conductive portions provided on an upper surface and a lower surface of the supporting plate;

the upper surface of the supporting plate is a surface of the supporting plate opposing the substrate holder;

the lower surface of the supporting plate is a surface of the supporting plate opposing the one electrode;

the plurality of the conductive portions provided on the upper surface of the supporting plate are in contact with the substrate holder;

the plurality of the conductive portions provided on the lower surface of the supporting plate are in contact with the one electrode; and

the shapes of the plurality of the conductive portions provided on the upper surface and the lower surface of the supporting plate are brush shapes.

7. (Original) A plasma CVD apparatus according to claim 1, wherein the heater is integrally attached to the one electrode.

8. (Original) A plasma CVD apparatus according to claim 1, wherein the one conductive member is attached to the one electrode.

9. (Original) A plasma CVD apparatus according to claim 1, wherein the one conductive member is attached to the substrate holder.

10. (Original) A plasma CVD apparatus according to claim 1, further comprising a container, and the anode electrode, the cathode electrode, the substrate holder and the one

conductive member being included in the container, the one conductive member being attached to an inner surface of the container.

11. (Original) A plasma CVD apparatus according to claim 1, further comprising a tension adjustment member, the one conductive member being attached to the tension adjustment member.

12. (Currently amended) A plasma CVD apparatus comprising an anode electrode and a cathode electrode, which is for forming a thin film on a substrate by performing plasma discharge between the anode electrode and the cathode electrode, comprising:

a substrate holder disposed between the anode electrode and the cathode electrode; and

a plurality of conductive members disposed between the substrate holder and one electrode of either the anode electrode or the cathode electrode, wherein

the substrate holder supports the substrate,

the plurality of conductive members are provided in parallel to each other between the one electrode and the ~~and the~~ substrate holder so as to cover a substantially entire space between the one electrode and the and the substrate holder, and

the plurality of conductive members are electrically connected to the one electrode and the substrate holder.

13. (Original) A plasma CVD apparatus according to claim 12, wherein shapes of the anode electrode and the cathode electrode are plate-like shapes.

14. (Original) A plasma CVD apparatus according to claim 12, wherein plasma discharge is performed between the anode electrode and the cathode electrode by applying a voltage between the anode electrode and the cathode electrode with a raw material gas supplied between the anode electrode and the cathode electrode.

15. (Previously presented) A plasma CVD apparatus according to claim 12, wherein:

the plurality of conductive members each include a supporting plate provided substantially parallel to the one electrode and a plurality of conductive plates provided on an upper surface and a lower surface of the supporting plate;

the upper surface of the supporting plate is a surface of the supporting plate opposing the substrate holder;

the lower surface of the supporting plate is a surface of the supporting plate opposing the one electrode;

the plurality of the conductive plates provided on the upper surface of the supporting plate are in contact with the substrate holder;

the plurality of the conductive plates provided on the lower surface of the supporting plate are in contact with the one electrode;

the shapes of the plurality of the conductive plates provided on the upper surface and the lower surface of the supporting plate are leaf-spring shapes;

the plurality of conductive plates are provided on the upper surface and the lower surface of the supporting plate by attaching one edge of each of the plurality of conductive plates to the supporting plate; and

the other edge of each of the plurality of the conductive plates is spaced from the supporting plate.

16. (Previously presented) A plasma CVD apparatus according to claim 12, wherein:

the plurality of conductive members each include a supporting plate provided substantially parallel to the one electrode and a plurality of conductive plates provided on an upper surface and a lower surface of the supporting plate;

the upper surface of the supporting plate is a surface of the supporting plate opposing the substrate holder;

the lower surface of the supporting plate is a surface of the supporting plate opposing the one electrode;

the plurality of the conductive plates provided on the upper surface of the supporting plate are in contact with the substrate holder;

the plurality of the conductive plates provided on the lower surface of the supporting plate are in contact with the one electrode;

the plurality of the conductive plates provided on the upper surface and the lower surface of the supporting plate are curved into arc shapes; and

the plurality of conductive plates are provided on the upper surface and the lower surface of the supporting plate by attaching one edge and the other edge of each of the plurality of conductive plates provided on the upper surface and the lower surface of the supporting plate to the supporting plate.

17. (Previously presented) A plasma CVD apparatus according to claim 12, wherein:

the plurality of conductive members each include a supporting plate provided substantially parallel to the one electrode and a plurality of conductive portions provided on an upper surface and a lower surface of the supporting plate;

the upper surface of the supporting plate is a surface of the supporting plate opposing the substrate holder;

the lower surface of the supporting plate is a surface of the supporting plate opposing the one electrode;

the plurality of the conductive portions provided on the upper surface of the supporting plate are in contact with the substrate holder;

the plurality of the conductive portions provided on the lower surface of the supporting plate are in contact with the one electrode; and

the shapes of the plurality of the conductive portions provided on the upper surface and the lower surface of the supporting plate are brush shapes.

18. (Original) A plasma CVD apparatus according to claim 12, wherein the heater is integrally attached to the one electrode.

19. (Original) A plasma CVD apparatus according to claim 12, wherein the plurality of conductive members are attached to the one electrode.

20. (Original) A plasma CVD apparatus according to claim 12, wherein the plurality of conductive members are attached to the substrate holder.

21. (Original) A plasma CVD apparatus according to claim 12, further comprising a container, and the anode electrode, the cathode electrode, the substrate holder and the plurality of conductive members being included in the container, the plurality of conductive members being attached to an inner surf ace of the container.

22. (Original) A plasma CVD apparatus according to claim 12, further comprising a tension adjustment member, the one conductive member being attached to the tension adjustment member.

23-26. (Canceled)

27. (Previously presented) The apparatus of claim 1, wherein the conductive member comprises a plurality of spaced apart conductive members that are in electrical communication with each other.

28. (Previously presented) The apparatus of claim 1, wherein the conductive member comprises a plurality of spaced apart leaf-spring like conductive plates, at least some of the leaf-spring like conductive plates contacting the one electrode.